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(54) **FILM FORMATION SOURCE, FILM FORMATION APPARATUS, FILM FORMATION METHOD, ORGANIC EL PANEL, AND METHOD OF MANUFACTURING ORGANIC EL PANEL**

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(57) **ABSTRACT**

It is an object of the invention to continuously perform, under a desired condition and for a long time period, a film formation process capable of producing a high quality film. A film formation apparatus comprises: a discharge outlet disposed within a film formation chamber and facing a film formation surface of a substrate; a material accommodating section disposed outside the film formation chamber and having material containers each containing a film formation material; a heating device for heating the film formation material contained within the material-containers; discharge passages which are air-tightly communicated with the discharge outlet and the material accommodating section; escape passages branching from the discharge passages for diverting the film formation material flowing towards the discharge outlet. On the downstream side of the branching positions of the discharge passages as well as on the escape passages, there are provided flow restricting valves capable of shutting off or passing the film formation material or variably adjusting the flow of the film formation material.

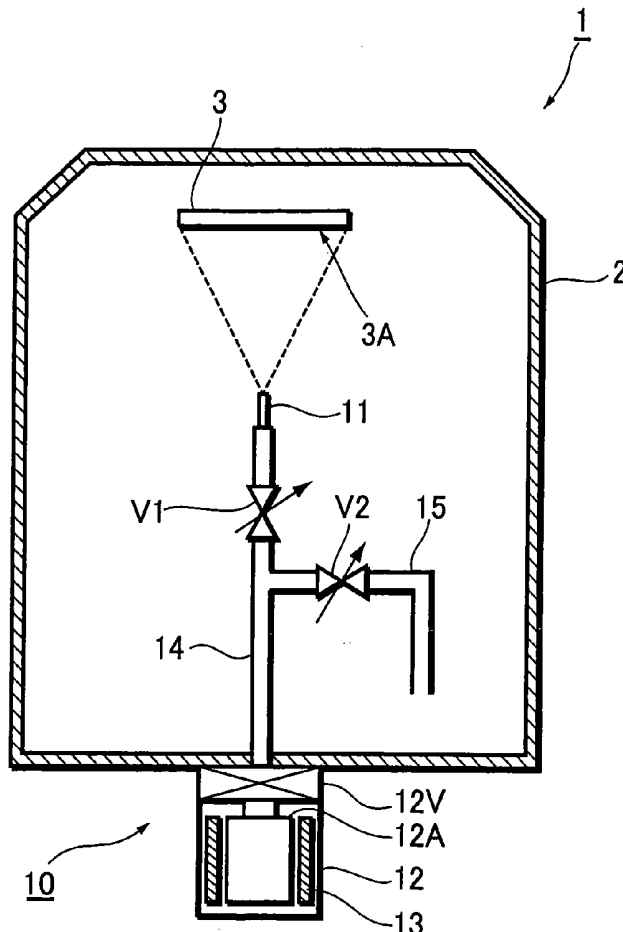


FIG. 1

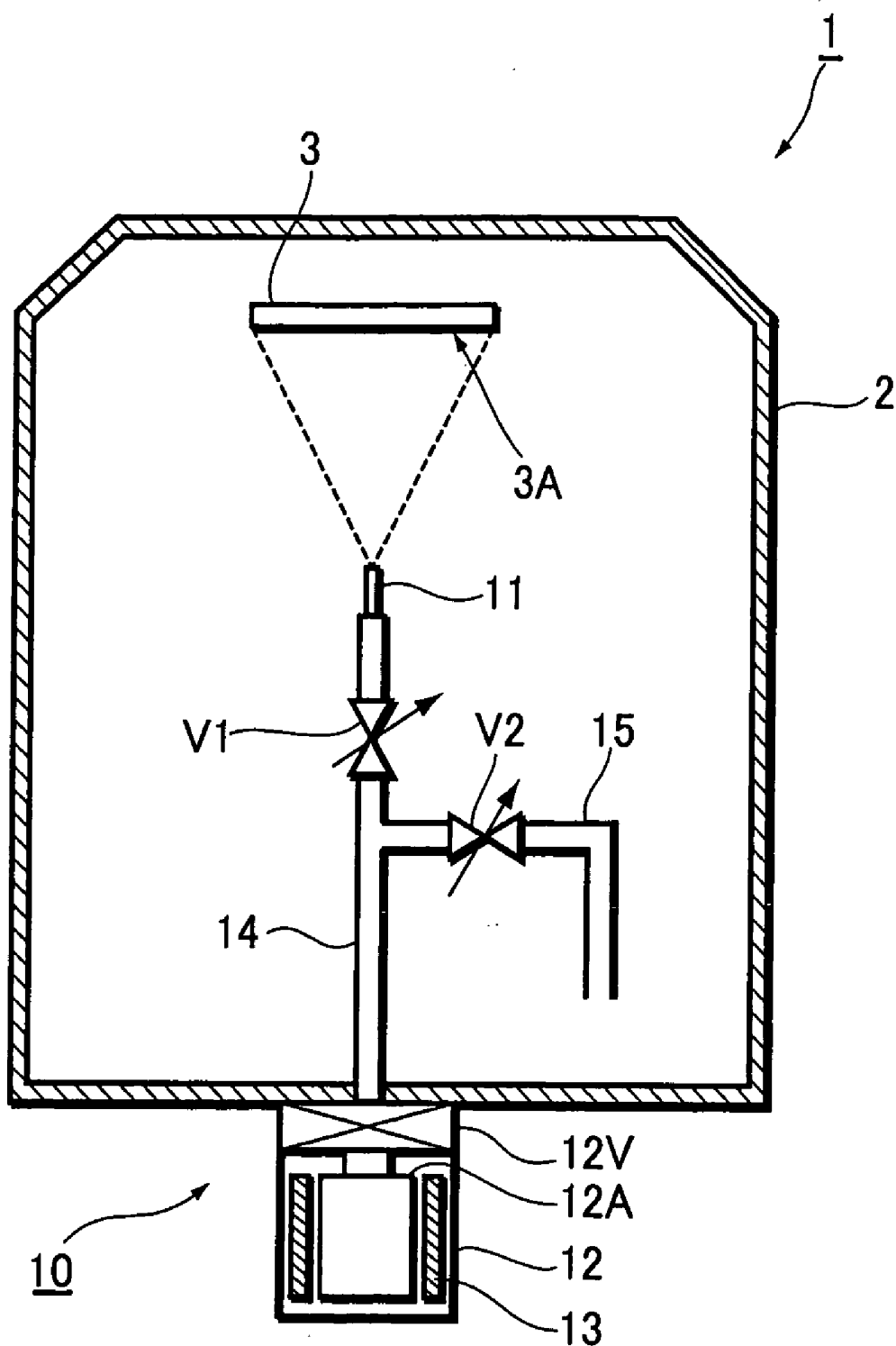


FIG.2

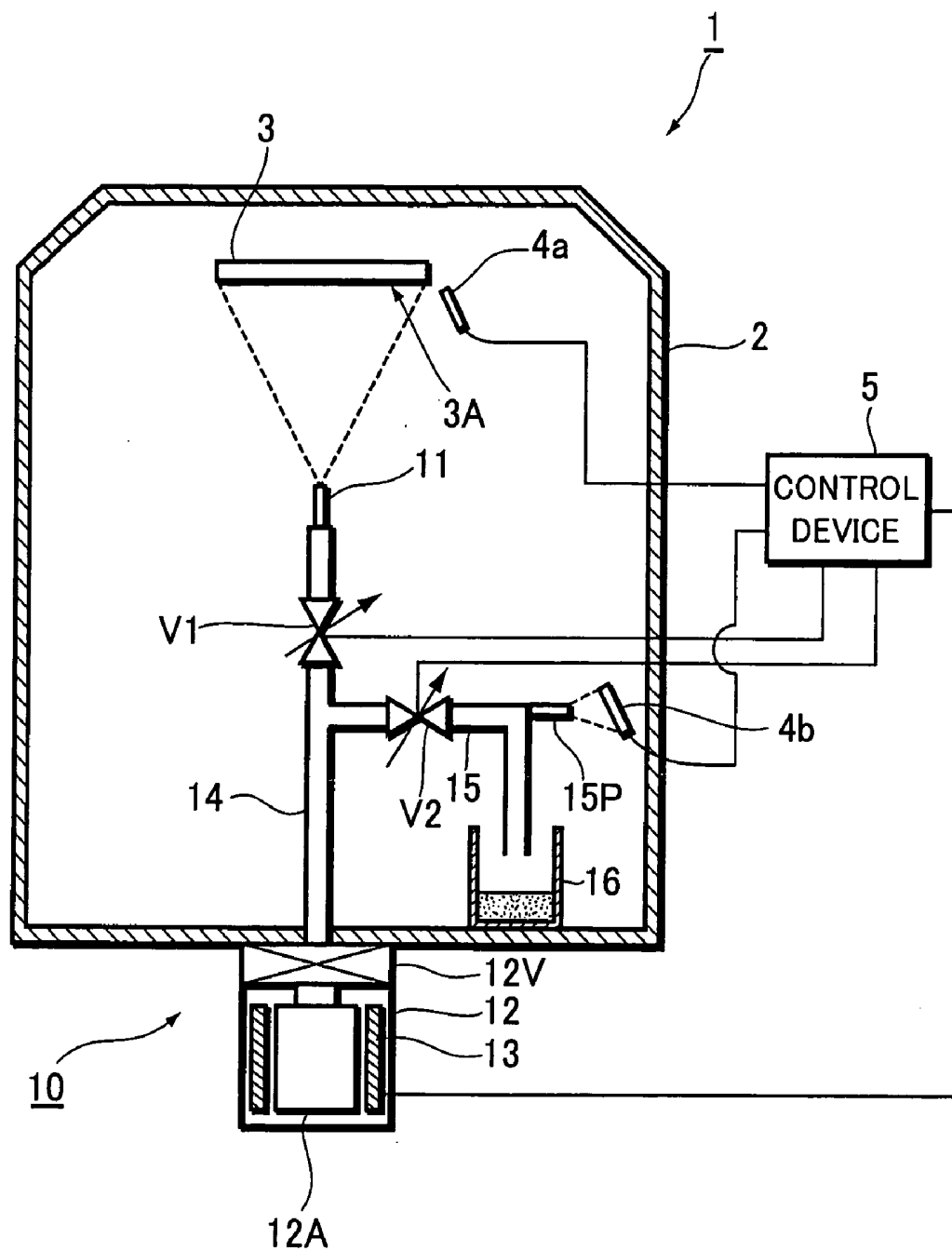
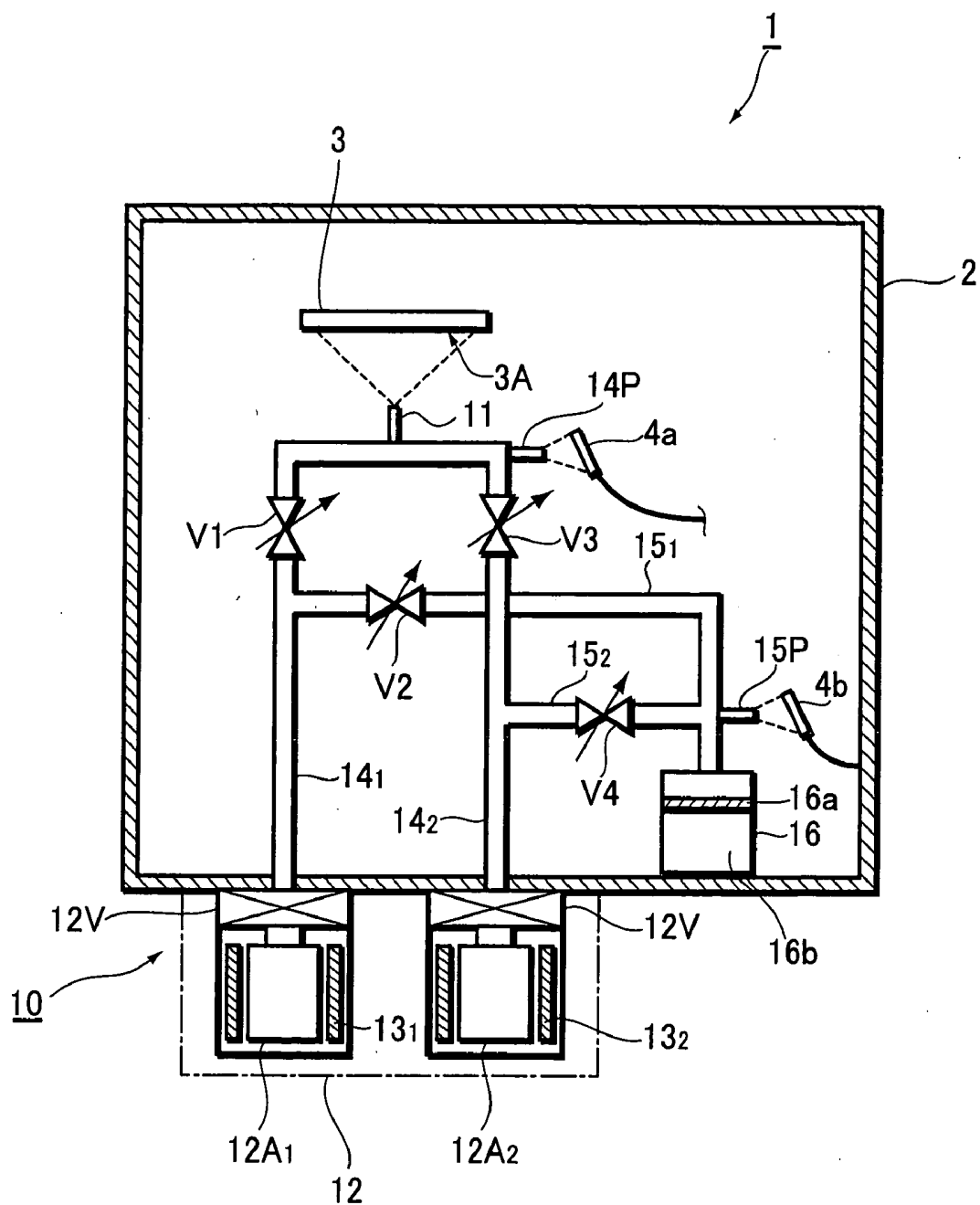


FIG. 3



FILM FORMATION SOURCE, FILM FORMATION APPARATUS, FILM FORMATION METHOD, ORGANIC EL PANEL, AND METHOD OF MANUFACTURING ORGANIC EL PANEL

BACKGROUND OF THE INVENTION

[0001] The present invention relates to a film formation source, a film formation apparatus, a film formation method, an organic EL panel, and a method of manufacturing the organic EL panel.

[0002] The present application claims priority from Japanese Application No. 2004-099944, the disclosures of which are incorporated herein by reference.

[0003] A film formation apparatus for forming a film of a solid material on a substrate is usually equipped with a film formation source containing a film formation material and located within a film formation chamber kept at a vacuum or depressurized state. Such a film formation apparatus may be a vacuum vapor deposition apparatus which heats a vapor deposition source positioned within a vacuum chamber, so that a deposition material discharged from an evaporation outlet of the vapor deposition source can be formed into a film on a substrate disposed within the vacuum chamber.

[0004] In view of the structure of such film formation apparatus or film formation source, it is understood that the vacuum condition within the vacuum chamber has to be broken each time a film formation material is supplemented to the film formation source. As a result, considerable time is needed for returning the internal atmosphere of the chamber to a desired condition when restarting the film formation, hence making it impossible to carry out the film formation with a high efficiency.

[0005] On the other hand, an organic EL panel manufacturing method which has drawn considerable attentions in the field of display or illumination, includes a step of forming a first electrode on a substrate, a step of forming thereon an organic material layer consisting of organic compounds, followed by forming thereon a second electrode. When forming an organic material layer or electrode layers, it is usual to carry out film formation steps using the above-described film formation apparatus. As a result, if a mass-production of such organic EL panel is to be carried out, the foregoing problem which occurs when supplementing film formation material becomes remarkable, rendering it impossible to ensure an acceptable productivity.

[0006] Moreover, each organic EL device serving as an essential element for an organic EL panel contains an organic material layer formed by a plurality of films having different functions. Further, an organic EL panel for multi-color displaying is formed in such a manner that organic EL devices consisting of different luminescent materials are formed on a substrate, so that it is necessary to perform film formation of different materials on a single substrate. However, since the above-described film formation apparatus or film formation source have been found difficult to carry out film formation of different materials in one chamber, it is necessary to employ a plurality of chambers, hence resulting in an enlarged scale of film formation apparatus and a complex manufacturing process.

[0007] In order to solve the problem mentioned above, Japanese Unexamined Patent Application Publication No.

2003-317957 has disclosed an improved vapor deposition apparatus in which one or more detachable vapor deposition sources are disposed outside a film formation chamber, a steam distributor having evaporation outlets is disposed within the chamber, a steam transporting system including valves is connected between each vapor deposition source and the steam distributor.

[0008] According to the above patent publication, when film formation material is supplied to the vapor deposition source or the deposition source is exchanged, it is not necessary to break the vacuum state within the chamber, so that it is allowed to shorten an operation time. Meanwhile, if the vapor deposition is switched over so that different material can be deposited, it is possible to perform film formations of different materials in single one chamber.

[0009] However, when the above-mentioned art is adopted, some problems which will be discussed below make it difficult to improve the workability and the operational precision of film formation process, the productivity and yield of an organic EL panel manufacturing process.

[0010] Namely, with regard to a film formation source in which a film formation material is sublimated or evaporated by heating, it is difficult for the film formation material to be discharged at a desired state even if heating is started, hence requiring a relatively long operation time until a desired discharge state is obtained. Moreover, even when heating has been stopped, it is still difficult to stop the discharge of the film formation material at once, hence requiring a relatively long time until the discharge gradually stops. In addition, when a film formation material contained in a film formation source has decreased, the discharge rate of the film formation material will also drop, hence rendering it impossible to ensure a desired discharge state. Besides, even if heating is carried out to control the discharge state of the film formation material, a relatively long operation time is required until a heated material is sublimated or evaporated so as to be discharged (as described above). As a result, a control system will become a system involving a large time constant, hence rendering it difficult to effectively control the discharge state of the film formation material only by controlling the heating.

[0011] In order to solve the above problem, the aforementioned prior art provides valve in material transport system for transporting the film formation material, thereby adjusting the discharge state by adjusting an opening degree of the valve. However, when the valve is provided in an airtight transport system which directs a film formation material (which is produced from a film formation source located outside the film formation chamber) to a discharge outlet of the film formation chamber, since the sublimation or evaporation of the film formation material is difficult to be decelerated at once even if the opening degree of valve is narrowed and a heating velocity is reduced, a reduction in the opening degree of the valve can increase an internal pressure of the film formation chamber. As a result, the material contained in the film formation source will be undesirably modified due to its decomposition or the like, rendering it impossible to effect an acceptable film formation. Besides, an operation pressure will go beyond a controllable range, making it impossible to perform an acceptable discharge rate control. Namely, in the above-described prior art, when valve is used to control the discharge state of

the film formation material, the film formation material contained within the film formation source will get deteriorated in its quality, an operation pressure will go beyond a controllable pressure range, hence rendering it impossible to perform an acceptable film formation.

[0012] Moreover, in response to an actual condition of film formation, it might be necessary to quickly shut off the film formation material flowing from the film formation source to a substrate. At this time, if merely the above-mentioned valve is closed, there will be an increase in an internal pressure of the film formation chamber and this can cause an undesired modification in the film formation material contained in the film formation source, and cause an operation pressure to go beyond a controllable range. As a result, it is impossible to carry out an acceptable film formation by using such a film formation source.

[0013] In order to avoid the above problem, it is possible to interpose a shielding member (shutter) between the discharge outlet and an object on which a film is formed. However, if this is realized, a considerable amount of film formation material will adhere to the shielding member, making it impossible to smoothly restart film formation and difficult to recover the adhered material. Besides, since the film formation material forming an organic material layer for an organic EL panel is expensive, an effort for increasing the recovery rate of a film formation material not used in the film formation process is extremely important for reducing the production cost.

[0014] On the other hand, according to the above-described prior art, before the film formation source disposed outside the film formation chamber is exchanged without using a valve to shut off the transport system, the film formation material is usually continued to be discharged until the material is used up, and the film formation source is then replaced by a new film formation source at the time the material has become zero. However, since it is impossible to ensure a desired discharge state and the film formation process has to be stopped temporally before and after the exchange of the film formation source, it is impossible to continuously perform the film formation operation while at the same time maintaining a desired film formation state (even if it is possible to exchange the film formation source) for a long time.

[0015] When a conventional film formation apparatus or a conventional film formation source having the above-described problem is used to manufacture an organic EL panel, since it is impossible to continuously maintain a desired film formation state for a long time, it is difficult to greatly improve the productivity of panel manufacturing process. Moreover, if such a conventional art is adopted to carry out a prolonged film formation operation, it is impossible to maintain an acceptable discharge state of film formation material, hence rendering it difficult to produce a high quality organic EL panel.

SUMMARY OF THE INVENTION

[0016] The present invention is to solve the above-discussed problem, and it is an object of the invention to perform a film formation process capable of producing an acceptable film, avoiding a deterioration of a film formation material when supplementing or exchanging the same, controlling the discharge state of the film formation material,

improving the productivity of an organic EL panel manufacturing process, and improving product yield by improving film formation precision.

[0017] In order to achieve the above objects, the present invention is characterized by at least the following aspects.

[0018] According to one aspect of the present invention, there is provided a film formation apparatus having a film formation chamber in which a vacuum or a depressurized state is formed and a sublimated or evaporated film formation material is formed into a film on a substrate, such film formation apparatus comprising: a discharge outlet disposed within the film formation chamber for discharging the film formation material towards a film formation surface of the substrate; a material accommodating section disposed outside the film formation chamber and including a material container containing the film formation material; a heating device for heating the film formation material contained in the material container; a discharge passage air-tightly communicating the discharge outlet with the material accommodating section; an escape passage branching from the discharge passage for diverting the film formation material moving towards the discharge outlet to a different direction; and flow restricting devices provided at least on the lower stream side of a branching position of the discharge passage and on the escape passage, for stopping/passing or variably adjusting the flow of the film formation material.

[0019] According to another aspect of the present invention, there is provided a film formation method in which a discharge outlet is caused to face a film formation surface of a substrate disposed within a film formation chamber kept at a vacuum or depressurized state, a film formation material sublimated or evaporated by heating in a material accommodating section disposed outside the film formation chamber is allowed to flow through a discharge passage and discharged from the discharge outlet so as to form a film on the film formation surface. In particular, an escape passage is provided by branching from the discharge passage for diverting the film formation material moving towards the discharge outlet to a different direction. Further, a flow through the escape passage is started when the flow of the film formation material is shut off or restricted on the lower stream side of a branching position of the discharge passage.

BRIEF DESCRIPTION OF THE DRAWINGS

[0020] These and other objects and advantages of the present invention will become clear from the following description with reference to the accompanying drawings, wherein:

[0021] FIG. 1 is an explanatory view showing the basic structure of a film formation source and a film formation apparatus employing the film formation source, according to one embodiment of the present invention;

[0022] FIG. 2 is another explanatory view showing a film formation source and a film formation apparatus employing the film formation source, according to another embodiment of the present invention shown in more detail than the above embodiment;

[0023] FIG. 3 is a further explanatory view showing a film formation source and a film formation apparatus employing the film formation source, according to a further embodiment of the present invention; and

[0024] FIG. 4 is an explanatory view showing an example of an organic EL panel manufactured in the apparatus and method of the present invention.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0025] Preferred embodiments of the present invention will be described below with reference to the accompanying drawings. FIG. 1 is an explanatory view showing a film formation source and the fundamental structure of a film formation apparatus containing the film formation source, according to one embodiment of the present invention. As shown, a film formation apparatus 1 comprises a film formation chamber 2 and a film formation source 10. In the film formation chamber 2 kept at a vacuum or depressurized state, a film formation material is sublimated or evaporated and formed into a film on a film formation surface 3A of a substrate 3.

[0026] The film formation source 10 comprises: a discharge outlet 11 disposed within the film formation chamber 2 for discharging the film formation material onto the film formation surface 3A of the substrate 3; a material accommodating section 12 disposed outside the film formation chamber 2 and having a material container 12A accommodating the film formation material; a heating device 13 (heating means) for heating the film formation material contained within the material container 12A; a discharge passage 14 which is air-tightly communicated with the discharge outlet 11 as well as with the material accommodating section 12; an escape passage 15 branching from the discharge passage 14 for diverting the film formation material flowing towards the discharge outlet 11. On the downstream side of the branching position of the discharge passage 14 as well as on the escape passage 15, there are provided flow restricting valves V1, V2 (means for restricting the flow of film formation material) capable of stopping or passing the film formation material or variably adjusting the flow of the film formation material.

[0027] The material accommodating section 12 is in an air-tight condition and provided with a gate valve 12V on the upper side thereof, with the material container 12A air-tightly connected to the discharge passage 14 using a metal gasket. Then, if the material container 12A is disconnected from the discharge passage 14 and the gate valve 12V is closed, it is allowed to open the material accommodating section 12 to the surrounding atmosphere to remove or exchange the material container 12A, without bringing about any change in the atmosphere within the film formation chamber 2. Moreover, the material accommodating section 12 can also be provided with an additional mechanism for vertically moving the material container 12A in order to connect or disconnect the same to or from the discharge passage 14. Further, although not shown in the accompanying drawings, the material accommodating section 12 and the material container 12A can be exhausted independently of the film formation chamber 2. Moreover, similar to the above-discussed prior art (Japanese Unexamined Patent Application Publication No. 2003-317957), it is allowed to employ an adjusting valve instead of the gate valve.

[0028] In the film formation method utilizing the film formation apparatus 1, film formation operation is per-

formed by completely opening the flow restricting valve V1 to open the discharge passage 14 and by closing the flow restricting valve V2 to shut the escape passage 15, so that the film formation material sublimated or evaporated by heating in the material accommodating section 12 disposed outside the film formation chamber 2, will flow through the discharge passage 14 and be discharged from the discharge outlet 11 to the film formation surface 3A, thus forming a desired film on one surface of the substrate 3. Further, if the flow through the discharge passage 14 is to be shut off or reduced by closing or narrowing the flow restricting valve V1, it is allowed to open the flow restricting valve V2 so as to start flowing through the escape passage 15.

[0029] In this way, by optionally adjusting the opening degree of the flow restricting valve V1, it is possible to freely adjust the discharge state (for example, vapor deposition rate) of the film formation material from the discharge outlet 11. At this time, by properly opening the flow restricting valve V2 on the escape passage 15 in response to the opening degree of the flow restricting valve V1, the film formation material throttled by the flow restricting valve V1 can escape to the escape passage 15. Therefore, it is possible to prevent the pressure within the material container 12A of the film formation source 10 from rising up, thus avoiding a deterioration of the film formation material within the material container 12A and preventing the film formation material from leaving a desired pressure range. Accordingly, even when the discharge state of the film formation material (for example, flow rate) has been changed (controlled), it is still possible to ensure a high quality film formation, without causing a deterioration of the film formation material and its departure from a desired flow rate range.

[0030] At the beginning of a heating process using the heating device 13, although it takes a certain time to reach a desired discharge state, the flow restricting valve V1 is closed to shut the discharge passage 14 while the flow restricting valve V2 is opened to open the escape passage 15, such a condition being continued until the discharge state from the material accommodating section 12 reaches a predetermined one. After the discharge from the material accommodating section 12 has reached a predetermined state, the flow restricting valve V1 is opened to open the discharge passage 14 while the flow restricting valve V2 is closed to shut the escape passage 15, so that film formation can be started and the discharge is controlled at a desired state, thereby ensuring a desired film formation from the beginning of the film formation process.

[0031] On the other hand, once the film formation material within the material container 12A decreases, it will become impossible to ensure a desired discharge state. At this time, if the flow restricting valve V1 is closed to shut the discharge passage 14 while the flow restricting valve V2 is opened to open the escape passage 15, it is possible to stop the discharge from the discharge outlet 11 before the discharge state gets worse, and to avoid a possible deterioration of the film formation material which is usually caused by a pressure change.

[0032] Although an example illustrated herein shows that the flow restricting valves V1, V2 and the escape passage 15 are provided within the film formation chamber 2, the present invention should not be limited by such a specific example. In fact, it is also possible for the flow restricting

valves V1, V2 and the escape passage 15 to be disposed outside the film formation chamber 2. At this time, the front end of the escape passage 15 should of course be held within a vacuum container other than the film formation chamber 2.

[0033] FIG. 2 is an explanatory view showing a film formation source and a film formation apparatus containing the film formation source, according to another embodiment of the present invention which is a more detailed example based on the above-described embodiment (elements which are the same as those described above will be represented by the same reference numerals and the related descriptions will be partially omitted).

[0034] Actually, this embodiment is characterized by a film formation material collection device 16 provided at the end of the escape passage 15. Namely, according to the film formation method using the film formation source 10 of the film formation apparatus 1 of the present embodiment, the film formation material collection device 16 is provided at the end of the escape passage 15, so that it is possible to collect the film formation material passing through the escape passage 15. In this way, since the film formation material collection device 16 can collect the film formation material passing through the escape passage 15, it is allowed to omit an additional step for recovering the unused material, thereby making it possible to effectively reuse the film formation material and thus improving the economical efficiency of the film formation process.

[0035] Although an example illustrated herein shows that the film formation material collection device 16 is installed within the film formation chamber 2, the present invention should not be limited by this. Actually, it is also possible to extend the escape passage 15 so that its front end is disposed on the outside of the film formation chamber 2 and the film formation material collection device 16 is allowed to be connected with the escape passage 15 outside the film formation chamber 2. In this way, it is possible to reuse the film formation material collected by the film formation material collection device 16 without breaking the vacuum state of the film formation chamber 2. Also, since it is possible to exchange the film formation material collection device 16 (filled with the film formation material) without breaking the vacuum state of the film formation chamber 2, it is allowed to improve the efficiency of the film formation process, thereby ensuring a smooth and continuous film formation operation.

[0036] Moreover, the present embodiment is characterized by providing, on one or each of the discharge passage 14 and the escape passage 15, a detection port 15P for detecting the flowing state of the film formation material, and detectors 4a, 4b (detection device, thickness monitoring device or the like) for detecting the film formation material in the vicinity of the substrate 3 or discharged from the detection port 15P. Furthermore, the film formation apparatus 1 has a control unit 5 (control device) for controlling the valves V1, V2 in accordance with the detection results of the detectors 4a, 4b. In addition, it is also possible for the control unit 5 to control the heating device 13 of the material accommodating section 12. Preferably, the control unit 5 can control both of the valves V1 and V2, as well as the heating device 13.

[0037] In this way, by using the detector 4a to detect the film formation material discharged from the discharge passage 14 and by controlling the opening degrees of the valves

V1, V2 in accordance with the detection results, it is possible to freely control the discharge state (for example, vapor deposition rate) from the discharge outlet 11, without decomposing the film formation material contained in the film formation source 10, nor causing an increased pressure higher than a predetermined range. For example, if it is detected that the discharge state from the discharge outlet 11 is at a high rate, the flow restricting valve V1 is closed to some extent, whereas the flow restricting valve V2 is opened, thereby inhibiting the high rate discharge state so as to obtain a uniform discharge rate, and controlling the inner pressure of the film formation source 10 within a desired pressure range which ensures an acceptable film formation.

[0038] Moreover, by using the detector 4b to detect the film formation material discharged from the detection port 15P (located on the downstream side of the flow restricting valve V2 of the escape passage 15), and by opening or closing the valves V1, V2 in accordance with the detection results, it is possible to perform a control to change one state (wherein the flow restricting valve V1 is closed and the flow restricting valve V2 is opened) to another (wherein the flow restricting valve V1 is opened and the flow restricting valve V2 is closed), in response to the discharge state (such as a standup state at the beginning of a heating process) from the material accommodating section 12.

[0039] Moreover, if the discharge from the discharge outlet 11 is to be stopped immediately as an urgent measure, the control unit 5 will operate to open the flow restricting valve V2 and at the same time close the flow restricting valve V1. At this time, if the heating device 13 is maintained at its operative state and if the valve V1 is opened and the valve V2 is closed, it is possible for the apparatus to quickly return back to its previous operation state existing before the stopping. On the other hand, if the apparatus does not require any urgent restoration for returning back, it is allowed to close the valve V1 and open the valve V2, as well as to stop the operation of the heating device 13.

[0040] In this way, since it is not necessary to employ any blocking member such as shutter during an urgent shut-off, it is possible to ensure a smooth operation for returning back. Meanwhile, since there would be no film formation material to adhere to a blocking member such as shutter, it is possible to ensure an easy recovery of the film formation material and thus an economical film formation process.

[0041] FIG. 3 is an explanatory view showing a film formation source formed according to another embodiment of the present invention and a film formation apparatus containing the film formation source (elements which are the same as those in the foregoing embodiment will be represented by the same reference numerals and the description thereof will be partially omitted).

[0042] In the present embodiment, the material accommodating section 12 has detachable or exchangeable material containers 12A₁ and 12A₂ which are connected with discharge passages 14₁ and 14₂ communicated with their common discharge outlet 11.

[0043] As shown, the first material container 12A₁ of the material accommodating section 12 disposed outside the film formation chamber 2 is connected with the discharge passage 14₁ and communicated with the discharge outlet 11 through the discharge passage 14₁, while the second material

container $12A_2$ is connected with the discharge passage 14_2 and communicated with the discharge outlet 11 through the discharge passage 14_2 .

[0044] Further, escape passages 15_1 , 15_2 are branching from the discharge passages 14_1 , 14_2 and are connected through their end portions to film formation material collection device 16 . Although an example illustrated herein shows that the escape passages 15_1 , 15_2 are communicated with each other at their end portions and connected to the film formation material collection device 16 , it is also possible to provide one film formation material collection device 16 at the end of each of the escape passages 15_1 , 15_2 . Moreover, in case where the material containers $12A_1$ and $12A_2$ are used to hold different materials, it is necessary for each of the escape passages 15_1 , 15_2 to have its own film formation material collection device 16 . Moreover, although an example illustrated herein shows that the film formation material collection device 16 is installed within the film formation chamber 2 , it is also possible to extend the escape passages 15_1 , 15_2 so that their end portions are disposed on the outside of the film formation chamber 2 , thereby allowing the film formation material collection device 16 to be installed outside the film formation chamber 2 .

[0045] Further, similar to the foregoing embodiment, the flow restricting valves $V1$ and $V2$ are provided on the discharge passage 14_1 of the first material container $12A_1$ and on the escape passage 15_1 , while the flow restricting valves $V3$ and $V4$ are provided on the discharge passage 14_2 of the second material container $12A_2$ and on the escape passages 15_2 .

[0046] Moreover, the material accommodating section 12 contains heating devices 13_1 and 13_2 located within the first material container $12A_1$ and the second material container $12A_2$. Further, a heat-insulator $16a$ is provided in the film formation material collection device 16 , while a cooling unit $16b$ is formed beneath the heat-insulator $16a$. Besides, although an example illustrated herein involves two material containers $12A_1$ and $12A_2$, it is also possible to include three or more material containers which have similar structures.

[0047] By using the film formation source 10 , the film formation apparatus 1 containing the film formation source 10 , and the method employing the film formation apparatus 1 , it is possible for each of the discharge passages 14_1 , 14_2 of the material containers $12A_1$, $12A_2$ as well as the escape passages 15_1 , 15_2 to obtain the same effect as obtained in the foregoing embodiment. As compared with the foregoing embodiment, the present embodiment is suitable for carrying out continuous film formation during a prolonged time.

[0048] Namely, according to the present embodiment, film formation material within the first material container $12A_1$ is heated by the heating device 13_1 so as to be discharged from the first material container $12A_1$. At this time, similar to the foregoing embodiment, the flow restricting valve $V1$ is closed and the flow restricting valve $V2$ is opened, so that it

is allowed to perform a pre-heating until the discharge from the first material container $12A_1$ reaches a desired state. After the discharge from the first material container $12A_1$ has reached a desired state, the flow restricting valve $V1$ is opened and the flow restricting valve $V2$ is closed, so as to discharge the film formation material from the first material container $12A_1$ through the discharge outlet 11 , thereby effecting the film formation on the film formation surface $3A$ of the substrate 3 .

[0049] In this way, a plurality of substrates 3 are allowed to be successively moved into the film formation chamber 2 so as to effect a continuous film formation. In this manner, the film formation material within the material container $12A_1$ will decrease and this makes it difficult to maintain the material discharge at a predetermined state. In order to maintain the material discharge at a predetermined state, pre-heating is started to heat the film formation material within the second material container $12A_2$. Namely, prior to shutting the discharge passage 14_1 of the first material container $12A_1$, heating is started to heat the film formation material in the second material container $12A_2$ until the discharge from the second material container $12A_2$ reaches a predetermined state. At this time, the flow restricting valve $V3$ is closed to shut the discharge passage 14_2 of the second material container $12A_2$, while the flow restricting valve $V4$ is opened to open the escape-passage 15_2 . Then, after the discharge from the second material container $12A_2$ has reached a predetermined state, the flow restricting valve $V3$ is opened to open the discharge passage 14_2 , while the flow-restricting valve $V4$ is closed to shut the escape-passage 15_2 .

[0050] Accordingly, prior to exchanging the first material container $12A_1$ it is allowed to pre-heat the second material container $12A_2$, so that when the discharge from the first material container $12A_1$ is stopped, the film formation material can be discharged from the second material container $12A_2$, thereby immediately enabling the film formation material to be discharged through the outlet 11 in a desired state. Preferably, the discharge changeover is performed during a period in which the discharge outlet 11 does not directly face the film formation surface $3A$ of the substrate 3 . In other words, the discharge changeover is preferred to be performed after a treated substrate has been moved away and before an untreated substrate is moved into the film formation chamber 2 . Alternatively, the discharge changeover is carried out with a shielding plate (such as shutter) interposed between the film formation surface $3A$ and the discharge outlet 11 .

[0051] Moreover, during the discharge changeover from the material container $12A_1$ to the material container $12A_2$, it is possible to perform an appropriate control of the flow restricting valves $V1$ - $V4$ in accordance with the detection results of detectors $4a$ and $4b$. At this time, the flow restricting valves $V1$ - $V4$ can be controlled at the states shown in the following Table 1.

TABLE 1

	V1	V2	V3	V4
STATE 1	OPEN	CLOSED	CLOSED	CLOSED
STATE 2	OPEN	CLOSED	CLOSED	OPEN

TABLE 1-continued

	V1	V2	V3	V4
STATE 3	OPEN	CLOSED	GRADUALLY OPENED	OPEN
STATE 4	GRADUALLY CLOSED	GRADUALLY OPENED	PARTIALLY OPENED	GRADUALLY CLOSED
STATE 5	CLOSED	OPEN	OPEN	CLOSED
STATE 6	CLOSED	CLOSED	OPEN	CLOSED

[0052] Therefore, it is possible for the material discharge from the discharge outlet **11** to be controlled within a minimum time period required only for the opening or closing of the valves, thereby ensuring a smooth changeover from the discharge out of the first material container **12A₁** to the discharge out of the second material container **12A₂**. Further, even when the discharge out of the first material container **12A₁** has been changed over to the discharge out of the second material container **12A₂**, there would be no deviation in the position of the discharge outlet **11** since the discharge outlet **11** is common to discharges from both the first material container **12A₁** and the second material container **12A₂**, thus allowing the substrate **3** and the detector **4a** to be fixed in their original positions.

[0053] If, after opening the discharge passage **14₂** of the second material container **12A₂**, the discharge passage **14₁** of the first material container **12A₁** is to be closed, since at this time the discharge from the first material container **12A₁** does not stop immediately even if the heating of the first material container **12A₁** is stopped, the discharge passage **14₁** shall be closed and the escape-passage **15₁** shall be opened, thereby allowing the film formation material collection device **16** to collect the remaining film formation material. Then, after the discharge from the first material container **12A₁** has been accumulated to some extent, the gate-valve **12V** in connection with the first material container **12A₁** is closed, so that the first material container **12A₁** may be removed to supplement the film formation material therein or replaced by a new material container. Subsequently, since it is allowed to perform similar changeover from the second material container **12A₂** to the first material container **12A₁**, a repeated operation makes it possible to perform continuous film formation under the same condition for a long time.

[0054] Moreover, if the present embodiment is further improved by controlling the discharge state in accordance with the detection result of the detector **4a** described in the embodiment of **FIG. 2**, it is possible to perform a high precision film formation for a long time period. In addition, if valve changeover is controlled in accordance with the detection result of the detector **4b**, it is possible to realize a continuous film formation for a long time by performing an automatic changeover.

[0055] Moreover, in the present embodiment, the film formation material contained in the first material container **12A₁** is the same as the film formation material contained in the second material container **12A₂**, so that it is possible to perform a continuous film formation for a long time period, as described above. However, if the film formation material contained in the first material container **12A₁** is different from the film formation material contained in the second

material container **12A₂**, it is possible to effect a smooth changeover from one film formation based on one film formation material to another film formation based on another film formation material, by virtue of the same effect as described above.

[0056] Here, each of the flow restricting valves **V1-V4** mentioned above can be formed by an independently variable adjusting valve. However, if it is difficult to ensure an adequate durability as well as an adequate reliability during full closure of valve, it is allowed to form a combination of ON-OFF valves (capable of effecting a changeover between closing and opening) with variable adjusting valves. Moreover, although not shown in the accompanying drawings, it is also possible to employ a three-way valve or a combination of the three-way valve with valves **V1** and **V2**. Besides, as to the flow restricting valves **V2, V4** provided on the escape passages **15, 15₁, 15₂**, it is allowed to use only ON-OFF valves capable of effecting a changeover between closing and opening (but not having variable adjusting function). In addition, the flow restricting valves **V1-V4** are not absolutely necessary to be valves, but can be replaced by other flow restricting device such as shutters.

[0057] Moreover, if necessary, it is also possible to provide heating device in one of other positions not included in the material accommodating section **12**, such as the discharge passages **14, 14₁, 14₂**, the escape passages **15, 15₁, 15₂**, the discharge outlet **11**, and the detection ports **14P, 15P**. In this way, it is possible to ensure smoother flowing or discharge of the film formation material from the material accommodating section **12**.

[0058] Further, the film formation apparatus **1** mentioned above may be a vacuum deposition apparatus using a resistance heating method, a high-frequency heating method, a laser heating method, or an electron beam heating method. However, a method for use in the vacuum deposition apparatus **1** should not be limited as such. For example, if the vacuum deposition apparatus employs a resistance heating method, the film formation chamber **2** may be a vacuum chamber set at a high vacuum condition (10^{-4} Pa or less), while the material accommodating section **12** may be a container formed by a high-melting point oxide such as alumina (Al_2O_3) and Beryllia (BeO), and surrounded by a heating device **13** consisting of high melting point filament such as tantalum (Ta), molybdenum (Mo), and tungsten (W), or consisting of a boat-like heating coil. Besides, the film formation may be a discontinuous process in which substrates are treated individually or an inline type process in which substrates are treated continuously.

[0059] Besides, although an example illustrated herein shows that the discharge outlet **11** is arranged to face upward and the film formation surface **3A** is arranged to face

downward, the present invention should not be limited by such a specific example. Actually, it is also possible for the discharge outlet **11** to face in the horizontal direction and the substrate **3** in an upright direction so that its film formation surface **3A** can face the discharge outlet **11**. Here, the discharge outlet can have any desired shape which may be circular or rectangular, and it is also possible to employ a plurality of such discharge outlets in order to continuously effect a uniform film formation on the film formation surface **3A**.

[0060] The above-described film formation apparatus **1** and the film formation method using the film formation apparatus **1** are suitable for manufacturing an organic EL panel. Such an organic EL panel includes a substrate and organic EL devices formed on the substrate, each organic EL device has a pair of electrodes including a first electrode and a second electrode, an organic layer interposed between the pair of electrodes, such an organic layer contains an organic luminescent layer. When at least one sort of film formation material for forming the electrodes or the organic material layer is formed into a film on the substrate **3**, it is allowed to use the above-described film formation apparatus **1** and the film formation method using the film formation apparatus **1**. In this way, since it is possible to effect a high precision film formation (for a long time period) on the film formation surface **3A** of each substrate **3** being successively moved into the film formation chamber **2**, it is possible to improve the productivity of an organic EL panel manufacturing process, thus improving the yield of production by improving the precision of film formation.

[0061] FIG. 4 is an explanatory view showing an example of an organic EL panel manufactured by the above-described manufacturing method.

[0062] As shown, the organic EL panel **100** is formed by interposing an organic layer **33** containing an organic luminescent layer between first electrodes **31** on one hand and second electrodes **32** on the other, thereby forming a plurality of organic EL devices **30** on the substrate **20**. In an example shown in FIG. 4, a silicone coating layer **20a** is formed on the substrate **20**, and a plurality of first electrodes **31** consisting of transparent electrode material such as ITO and serving as cathodes are formed on the silicon coating layer **20a**. Further, second electrodes **32** consisting of a metal and serving as anodes are formed above the first electrodes **31**, thereby forming a bottom emission type panel producing light from the substrate **20** side. Moreover, the panel also contains an organic layer **33** including a hole transporting layer **33A**, a luminescent layer **33B**, and an electron transporting layer **33C**. Then, a cover **40** is bonded to the substrate **20** through an adhesive layer **41**, thereby forming a sealing space **M** on the substrate **20** and thus forming a display section consisting of organic EL devices **30** within the sealing space **M**.

[0063] In the example shown in FIG. 4, the organic EL devices **30** are formed such that the first electrodes **31** are separated by a plurality of insulating strips **34**, thereby forming luminescent units (**30R**, **30G**, **30B**) under the first electrodes **31**. Moreover, a desiccant layer **42** is attached to the inner surface of the cover **40**, thereby preventing the organic EL devices **30** from getting deteriorated due to moisture.

[0064] Moreover, along the edge of the substrate **20** there is formed a first electrode layer **21A** using the same material

and the same step as forming the first electrodes **31**, which is separated from the first electrodes **31** by the insulating strips **34**. Further, on the lead-out portion of the first electrode layer **21A** there is formed a second electrode layer **21B** containing a silver-palladium (Ag—Pd) alloy and forming a low-resistant wiring portion. In addition, if necessary, a protection coating layer **21C** consisting of IZO or the like is formed on the second electrode layer **21C**. In this way, a lead-out electrode **21** can be formed which consists of the first electrode layer **21A**, the second electrode layer **21B**, and the protection coating **21C**. Then, an end portion **32a** of each second electrode **32** is connected to the lead-out electrode **21** within the sealing space **M**.

[0065] Here, although the lead-out electrode of each first electrode **31** is not shown in the drawing, it is possible to elongate each first electrode **31** and lead the same out of the sealing space **M**. Actually, such lead-out electrode can also be formed into an electrode layer containing Ag—Pd alloy or the like and constituting a low resistant wiring portion.

[0066] Next, description will be given to explain in detail the organic EL panel **100** and the method of manufacturing the same, according to one embodiment of the present invention.

[0067] a. Electrodes

[0068] Either the first electrodes **31** or the second electrodes **32** are set as cathode side, while the opposite side is set as anode side. The anode side is formed by a material having a higher work function than the cathode side, using a transparent conductive film which may be a metal film such as chromium (Cr), molybdenum (Mo), nickel (Ni), and platinum (Pt), or a metal oxide film such as ITO and IZO. In contrast, the cathode side is formed by a material having a lower work function than the anode side, using a metal having a low work function, which may be an alkali metal (such as Li, Na, K, Rb, and Cs), an alkaline earth metal (such as Be, Mg, Ca, Sr, and Ba), a rare earth metal, a compound or an alloy containing two or more of the above elements, or an amorphous semiconductor such as a doped polyaniline and a doped polyphenylene vinylene, or an oxide such as Cr₂O₃, NiO, and Mn₂O₃. Moreover, when the first electrodes **31** and the second electrodes **32** are all formed by transparent materials, it is allowed to provide a reflection film on one electrode side opposite to the light emission side.

[0069] The lead-out electrodes (the lead-out electrode **14** and the lead-out electrode of the first electrodes **31**) are connected with drive circuit parts driving the organic EL panel **100** or connected with a flexible wiring board. However, it is preferable for these lead-out electrodes to be formed as having a low resistance. Namely, the lead-out electrodes can be formed by laminating low resistant metal electrode layers which may be Ag—Pd alloy or APC, Cr, Al, or may be formed by single one electrode of low resistant metal.

[0070] b. Organic Layer

[0071] Although the organic layer **33** comprises one or more layers of organic compound materials including at least one organic luminescent layer, its laminated structure can be in any desired arrangement. Usually, as shown in FIG. 4, there is a laminated structure including, from the anode side towards the cathode side, a hole transporting layer **33A**, a luminescent layer **33B**, and an electron trans-

porting layer 33C. Each of the hole transporting layer 33A, the luminescent layer 33B, and the electron transporting layer 33C can be in a single-layer or a multi-layered structure. Moreover, it is also possible to dispense with the hole transporting layer 33A and/or the electron transporting layer 33C. On the other hand, if necessary, it is allowed to insert other organic layers including a hole injection layer, an electron injection layer and a carrier blocking layer. Here, the hole transporting layer 33A, the luminescent layer 33B, and the electron transporting layer 33C can be formed by any conventional materials (it is allowed to use either a high molecular material or a low molecular material).

[0072] With regard to a luminescent material for forming the luminescent layer 4B, it is allowed to make use of a luminescence (fluorescence) when the material returns from a singlet excited state to a base state or a luminescence (phosphorescence) when it returns from a triplet excited state to a base state.

[0073] c. Covering Member (Covering Film)

[0074] Further, the organic EL panel 100 according to the present invention is a panel formed by tightly covering organic EL devices 30 with a covering member 40 made of metal, glass, or plastic. Here, the covering member may be a piece of material having a recess portion (a one-step recess or a two-step recess) formed by pressing, etching, or blasting. Alternatively, the covering member may be formed by using a flat glass plate and includes an internal covering space M to be formed between the flat glass plate and the substrate by virtue of a spacer made of glass (or plastic).

[0075] In order to tightly seal the organic EL devices 30, it is also possible for the covering member 40 to be replaced by a sealing film to cover the organic EL devices 30. The covering film can be formed by laminating a single layer of protection film or a plurality of protection films, and is allowed to be formed by either an inorganic material or an organic material. Here, an inorganic material may be a nitride such as SiN, AlN, and GaN, or an oxide such as SiO, Al₂O₃, Ta₂O₅, ZnO, and GeO, or an oxidized nitride such as SiON, or a carbonized nitride such as SiCN, or a metal fluorine compound, or a metal film, etc. On the other hand, an organic material may be an epoxy resin, or an acryl resin, or a paraxylene resin, or a fluorine system high molecule such as perfluoro olefin and perfluoro ether, or a metal alkoxide such as CH₃OM and C₂H₅OM, or a polyimide precursor, or a perylene system compound, etc. In practice, the above-mentioned lamination and material selection can be carried out by appropriately designing the organic EL devices.

[0076] d. Adhesive Agent

[0077] An adhesive agent forming the adhesive layer 41 may be a thermal-setting type, a chemical-setting type (2-liquid mixture), or a light (ultraviolet) setting type, which can be formed by an acryl resin, an epoxy resin, a polyester, a polyolefine. Particularly, it is preferable to use an ultraviolet-setting epoxy resin adhesive agent which is quick to solidify without a heating treatment.

[0078] e. Desiccating Material

[0079] Desiccating material 42 may be a physical desiccating agent such as zeolite, silica gel, carbon, and carbon nanotube; a chemical desiccating agent such as alkali metal

oxide, metal halogenide, peroxide chlorine; a desiccating-agent formed by dissolving an organic metallic complex in a petroleum system solvent such as toluene, xylene, an aliphatic organic solvent and the like; and a desiccating agent formed by dispersing desiccating particles in a transparent binder such as polyethylene, polyisoprene, polyvinyl thinnate.

[0080] f. Various Types of Organic EL Display Panels

[0081] The organic EL panel 100 of the present invention can have various types without departing from the scope of the invention. For example, the light emission type of an organic EL device 30 can be a bottom emission type emitting light from the substrate 20 side, or a top emission type emitting light from a side opposite to the substrate 20. Moreover, the EL display panel may be a single color display or a multi-color display. In practice, in order to form a multi-color display panel, it is allowed to adopt a discriminated painting method or a method in which a single color (white or blue) luminescent layer is combined with a color conversion layer formed by a color filter or a fluorescent material (CF method, CCM method), a photo breaching method which realizes a multiple light emission by emitting an electromagnetic wave or the like to the light emission area of a single color luminescent layer, or SOLED (transparent Stacked OLED) method in which two or more colors of unit display areas are laminated to form one unit display area.

[0082] According to the above-described embodiments of the present invention, at the time of supplementing film formation material to the film formation source 10 or exchanging the film formation source, since it is not necessary to break a vacuum condition or a reduced pressure condition within the film formation chamber 2, it is allowed to shorten an operation time for performing the film formation, thereby ensuring an increased efficiency for the film formation operation. Further, even if the material containers 12A, 12A₁ and 12A₂ of the film formation source 10 are changed over to different materials, film formations using different materials can still be carried out within the same film formation chamber 2.

[0083] Moreover, since there is no pressure rise within the material containers 12A, 12A₁, and 12A₂ even at the time of controlling or stopping the discharge of the film formation material from the discharge outlet 11, there would not be any trouble in the quality of the film formation material, nor any departure from the predetermined pressure range, even when the film formation material is supplemented or exchanged or when the discharge of the film formation material is shut or controlled. Further, even when the material containers 12A₁ and 12A₂ are changed over to different materials, it is still possible to continue the film formation operation without stopping or changing the film formation condition. In this way, it is possible to continuously perform, under a desired condition and for a long time period, a film formation process capable of producing a high quality film.

[0084] In this way, by virtue of the organic EL panel manufacturing process including a film formation step using various materials, it is possible to improve the productivity and thus reduce production cost. Moreover, it is possible to improve the film formation precision and thus increase product yield. Further, since the use of the film formation material collection device 16 makes it possible to increase

the recovery rate of the material discharged but not used in the film formation, it is sure to reduce the production cost.

[0085] While there has been described what are at present considered to be preferred embodiments of the present invention, it will be understood that various modifications may be made thereto, and it is intended that the appended claims cover all such modifications as fall within the true spirit and scope of the invention.

What is claimed is:

1. A film formation source for use in a film formation apparatus having a film formation chamber in which a vacuum or a depressurized state is formed and a sublimated or evaporated film formation material is formed into a film on a substrate, said film formation source comprising:

- a discharge outlet disposed within the film formation chamber for discharging the film formation material towards a film formation surface of the substrate;
- a material accommodating section disposed outside the film formation chamber and including a material container containing the film formation material;
- a heating device for heating the film formation material contained in the material container;
- a discharge passage air-tightly communicating the discharge outlet with the material accommodating section;
- an escape passage branching from the discharge passage for diverting the film formation material moving towards the discharge outlet to a different direction; and
- flow restricting devices provided at least on the lower stream side of a branching position of the discharge passage and on the escape passage, for stopping/passing or variably adjusting the flow of the film formation material.

2. The film formation source according to claim 1, wherein a film formation material collection device is disposed at one end of the escape passage.

3. The film formation source according to claim 2, wherein the film formation material collection device is disposed outside the film formation chamber.

4. The film formation source according to claim 1, wherein the material accommodating section includes a plurality of detachable or exchangeable material containers, while a plurality of discharge passages are provided in connection with the material containers and communicated with a common discharge outlet.

5. The film formation source according to claim 1, wherein on the discharge passage and/or the escape passage there are provided a detecting port for detecting a flowing state of the film formation material, as well as a detecting device for detecting the film formation material discharged from the detecting port.

6. The film formation source according to claim 5, further comprising a control device for controlling the flow restricting devices, which control device operates to control the flow restricting devices in accordance with detection result of the detecting device.

7. A film formation apparatus comprising a film formation source recited in any one of claims 1 to 6 and a film formation chamber in which a vacuum or a depressurized state can be formed.

8. A film formation method in which a discharge outlet is caused to face a film formation surface of a substrate disposed within a film formation chamber kept at a vacuum or depressurized state, a film formation material sublimated or evaporated by heating in a material accommodating section disposed outside the film formation chamber is allowed to flow through a discharge passage and discharged from the discharge outlet so as to form a film on the film formation surface,

wherein an escape passage is provided by branching from the discharge passage for diverting the film formation material moving towards the discharge outlet to a different direction,

wherein a flow through the escape passage is started when the flow of the film formation material is shut off or restricted on the lower stream side of a branching position of the discharge passage.

9. The film formation method according to claim 8,

wherein the discharge passage is kept closed and the escape passage is kept open until a discharge state from the material accommodating section reaches a predetermined state,

wherein after the discharge state from the material accommodating section has reached a predetermined state, the discharge passage is opened and the escape passage is closed.

10. The film formation method according to claim 8,

wherein the material accommodating section includes a plurality of detachable or exchangeable material containers, while a plurality of discharge passages are provided in connection with the material containers and communicated with a common discharge outlet,

wherein before shutting a discharge passage communicated with a first material container of the material accommodating section, heating is started to heat a second material container of the material accommodating section,

wherein a discharge passage communicated with a second material container is kept closed and an escape passage branching from the discharge passage is kept open until a discharge state from the second material container reaches a predetermined state,

wherein after the discharge state from the second material container has reached a predetermined state, the discharge passage communicated with the second material container is opened and the escape passage branching from the discharge passage is closed.

11. The film formation method according to claim 10, wherein after the discharge passage communicated with the second material container is opened, the escape passage branching from the discharge passage communicated with the first material container is also opened, and the discharge passage communicated with the first material container is closed.

12. The film formation method according to claim 8, wherein the discharge outlet and the film formation surface of the substrate are caused not to face each other, and the discharge through the escape passage communicated with the first material container is changed over to the discharge through the discharge passage communicated with the second material container.

13. The film formation method according to claim 8, wherein a film formation material collection device is disposed at the end of the escape passages to collect the film formation material passing through the escape passages.

14. A method of manufacturing an Organic EL panel comprising a substrate and at least one organic EL device formed on the substrate, said at least one organic EL device including a first electrode, a second electrode, and an organic material layer interposed between the first and second electrodes, said organic material layer containing an organic luminescent layer,

wherein at least one kind of film formation material for forming the first electrode, the second electrode or the organic material layer is formed into a film on the substrate, using a film formation apparatus according to claim 7.

15. An organic EL panel comprising a substrate and at least one organic EL device formed on the substrate, said at least one organic EL device including a first electrode, a second electrode, and an organic material layer interposed between the first and second electrodes, said organic material layer containing an organic luminescent layer,

wherein the first electrode, the second electrode or the organic material layer is formed as a film on the substrate, using the organic EL panel manufacturing method according to claim 14.

16. A method of manufacturing an organic EL panel comprising a substrate and at least one organic EL device formed on the substrate, said at least one organic EL device including a first electrode, a second electrode, and an organic material layer interposed between the first and second electrodes, said organic material layer containing an organic luminescent layer,

wherein at least one kind of film formation material for forming the first electrode, the second electrode or the organic material layer is formed into a film on the substrate, using a film formation apparatus according to a film formation method according to any one of claims 8 to 13.

17. An organic EL panel comprising a substrate and at least one organic EL device formed on the substrate, said at least one organic EL device including a first electrode, a second electrode, and an organic material layer interposed between the first and second electrodes, said organic material layer containing an organic luminescent layer,

wherein the first electrode, the second electrode or the organic material layer is formed as a film on the substrate, using the organic EL panel manufacturing method according to claim 16.

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专利名称(译)	成膜源，成膜装置，成膜方法，有机EL面板，有机EL面板的制造方法		
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摘要(译)

本发明的一个目的是在所需条件下和长时间内连续进行能够生产高质量薄膜的成膜方法。一种成膜装置，包括：排出口，设置在成膜室内并面向基板的成膜表面；材料容纳部分，设置在成膜室外部，并且具有各自包含成膜材料的材料容器；加热装置，用于加热容纳在材料容器内的成膜材料；排出通道与排出口和材料容纳部分气密连通；从排出通道分支的逸出通道用于转移流向排出口的成膜材料。在排出通道的分支位置的下游侧以及排出通道上，设置有能够关闭或通过成膜材料或可变地调节成膜材料流动的流动限制阀。

